

L Number	Hits	Search Text	DB	Time stamp
1	1287	438/197	USPAT	2004/05/28 13:22
2	192	438/249	USPAT	2004/05/28 13:22
3	212	438/251	USPAT	2004/05/28 13:22
4	2122	438/257	USPAT	2004/05/28 13:22
5	483	438/267	USPAT	2004/05/28 13:22
6	842	438/289	USPAT	2004/05/28 13:22
7	1866	438/303	USPAT	2004/05/28 13:23
8	2399	438/305	USPAT	2004/05/28 13:23
9	887	438/306	USPAT	2004/05/28 13:23
10	719	438/307	USPAT	2004/05/28 13:23
11	332	438/311	USPAT	2004/05/28 13:23
12	1002	438/680	USPAT	2004/05/28 13:23
13	487	438/681	USPAT	2004/05/28 13:23
14	346	438/663	USPAT	2004/05/28 13:24
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16	1	("6323094").PN.	USPAT	2004/05/28 13:25
17	1	("6221746").PN.	USPAT	2004/05/28 13:25
18	1	("6214656").PN.	USPAT	2004/05/28 13:27
19	1	("6153520").PN.	USPAT	2004/05/28 13:27
20	1	("6008099").PN.	USPAT	2004/05/28 13:27
21	1	("5920774").PN.	USPAT	2004/05/28 13:28
22	1	("5792699").PN.	USPAT	2004/05/28 13:29
23	1	("5726477").PN.	USPAT	2004/05/28 13:29
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-	1	MOSFET and LDD and source and drain and region and tilt and angle and ion and doping and dope and dopant and spacer and gate and electrode and polysilicon and insulating and dielectric and thermal and LPCVD and PECVD and rapid	USPAT	2004/05/26 15:28
-	1		USPAT	2004/05/26 15:13
-	1		USPAT	2004/05/26 15:14
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-	1		USPAT	2004/05/26 15:14
-	1		USPAT	2004/05/26 15:15
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-	1	"5672525".PN. and (MOSFET or tilt or angle or polysilicon or gate or electrode or insulating or oxide or silicon or GaAs or SOI or source or drain or region or LDD or doping or doped or dopant or spacer or dielectric or diffusion or diffusing or thermal or treatment or rapid or LPCVD or PECVD or temperature)	USPAT	2004/05/26 15:41

-	1	"6352912".PN. and (MOSFET or tilt or angle or polysilic n or gate or electrode or insulating or oxide or silicon or GaAs or SOI or source or drain or region or LDD r doping or d ped or dopant or spacer or dielectric or diffusion or diffusing orthermal or treatment or rapid or LPCVD r PECVD or temperature)	USPAT	2004/05/26 15:42
-	1	(MOSFET and LDD and source and drain and region and tilt and angle and ion and doping and dope and dopant and spacer and gate and electrode and polysilicon and insulating and dielectric and thermal and LPCVD and PECVD and rapid) and (MOSFET or tilt or angle or polysilicon or gate or electrode or insulating or oxide or silicon or GaAs or SOI or source or drain or region or LDD or doping or doped or dopant or spacer or dielectric or diffusion or diffusing orthermal or treatment or rapid or LPCVD or PECVD or temperature)	USPAT	2004/05/28 13:22

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